

Amendments to the Specification

Applicants respectfully submit the following amendments to the specification in accordance with 37 C.F.R. § 1.121.

Please replace the paragraph on page 7, lines 1 – 14 of the specification with the following amended replacement paragraph:

As shown in Figure 4, a pseudo spin valve memory device 10 has a substrate 12, a seed layer 14, a magnetic storage layer 16, a non-magnetic, electrically conductive layer 18, and a magnetic sense layer 20. The seed layer ~~[[12]]~~ 14 may be formed, such as by sputter deposition of silicon oxide(s), silicon nitride or tantalum, on the substrate 12. The substrate ~~[[14]]~~ 12 may be silicon. The seed layer ~~[[12]]~~ 14 is optional. The magnetic storage layer 16, for example, may be a ferromagnetic alloy or multilayer such as NiFeCo, NiFe/CoFe, NiFe, or CoFe, and the magnetic storage layer 16 may have a thickness, for example, of between ~~[[1nm]]~~ 1 nm and 10 nm. The magnetic storage layer 16 is used to write the data stored in the pseudo spin valve memory device 10.

Please replace the paragraph on page 11, line 21 – page 12, line 13 of the specification with the following amended replacement paragraph:

The mask 80 is used to make each layer of the pseudo spin valve memory device 10. Thus, the mask 80 is used to make magnetic storage layer 16, the non-magnetic, electrically conductive layer 18, and the magnetic sense layer 20. These layers can be processed together ~~[[is]]~~ in a single lithographic patterning step or separately, as desired. The mask 80 with the stepped or rectangular bit end sections 86 and 88 results in pseudo spin valve memory devices

having fewer errors and higher yields. For example, uncertainty of the taper design is reduced because of the matching of the dimensions of the rectangular steps to the mask and fabrication technology. Moreover, the steps of the mask 80 as shown in Figure 7 can be arranged to produce [[bits]] bit ends having the desired bit end profile and using desired criteria such as linear, quadratic, and higher ordered or other profiles or shapes.